

Chip Termination 200 Watts, 50Ω



Description

The A200N50X4 is high performance Aluminum Nitride (AlN) chip termination intended as a cost competitive alternative to Beryllium Oxide (BeO). The termination is well suited to all cellular frequency bands such as; AMPS, GSM, DCS, PCS, PHS and UMTS. The high power handling makes the part ideal for terminating circulators and for use in power combiners. The termination is also RoHS compliant!

Features:

- RoHS Compliant
- 200 Watts
- DC - 2.2 GHz
- AlN Ceramic
- Non-Nichrome Resistive Element
- Low VSWR
- 100% Tested

General Specifications

Resistive Element	Thick film
Substrate	AlN Ceramic
Terminal Finish	Matte Tin over Nickel Barrier
Operating Temperature	-50 to +200°C (see de rating chart)

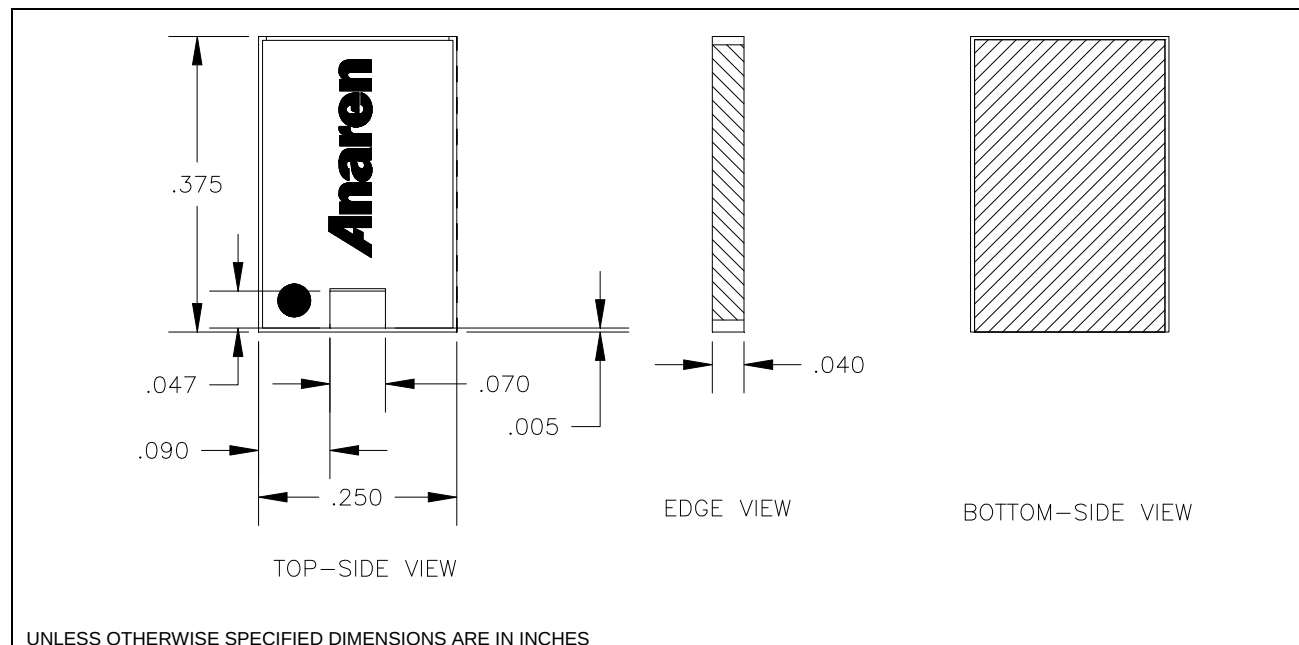
Tolerance is ± 0.010 ", unless otherwise specified. Designed to meet or exceed applicable portions of MIL-E-5400. All dimensions in inches.

Electrical Specifications

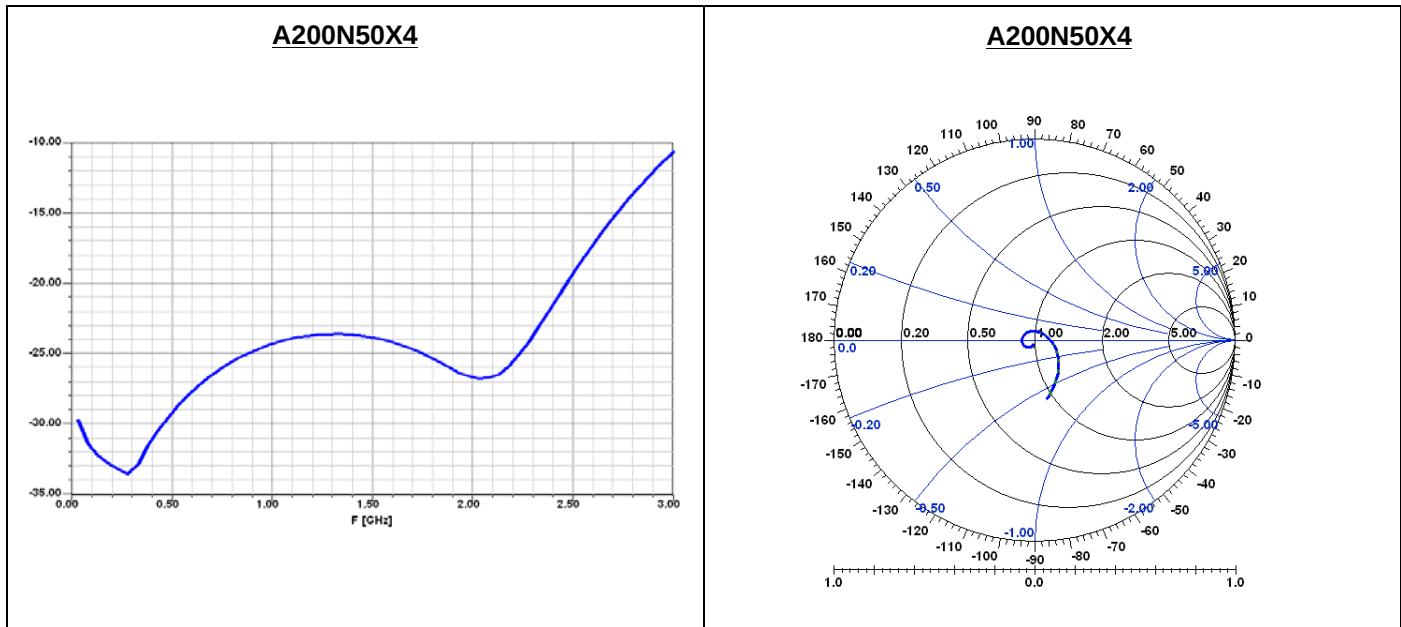
Resistance Value:	50 Ohms, $\pm 2\%$
Power:	200 Watts
Frequency Range:	DC – 2.2 GHz
Return Loss	> 20 dB DC – 2.2 GHz

Specification based on unit properly installed using suggested mounting instructions and a 50 ohm nominal impedance. **Specifications subject to change.**

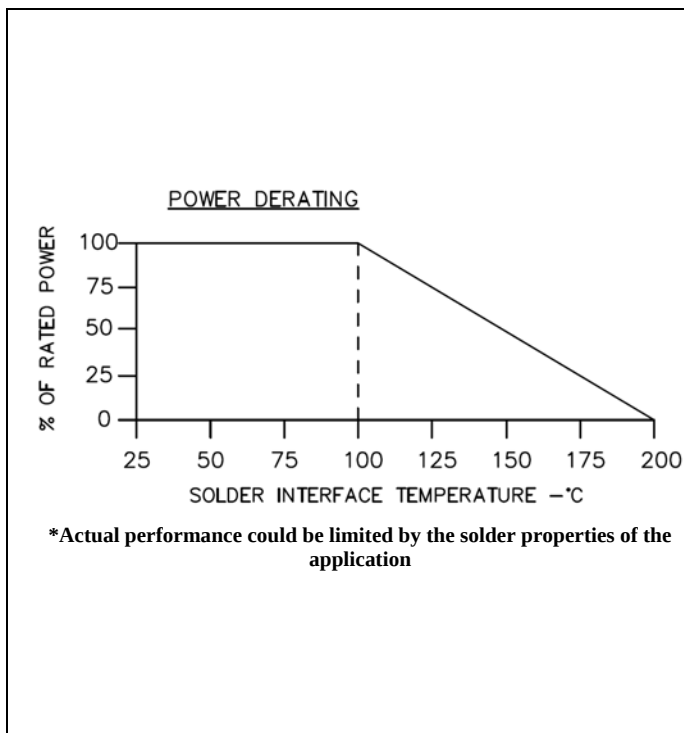
Outline Drawing



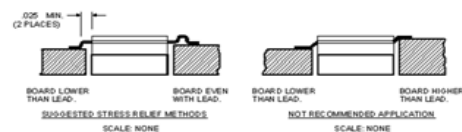
Typical Performance:



Power De-rating:



Mounting Footprint and Procedure:



SUGGESTED MOUNTING PROCEDURE

1. MAKE SURE THAT THE DEVICES ARE MOUNTED ON FLAT SURFACES (.001" UNDER THE DEVICE) TO OPTIMIZE THE HEAT TRANSFER.
2. POSITION DEVICE ON MOUNTING SURFACE AND SOLDER IN PLACE USING AN APPROPRIATE SOLDER.
3. SOLDER LEADS IN PLACE USING AN APPROPRIATE SOLDER TYPE WITH A CONTROLLED TEMPERATURE IRON.